

University of New Mexico
Department of Electrical and Computer Engineering

ECE 321 – Electronics I (Fall 2012)

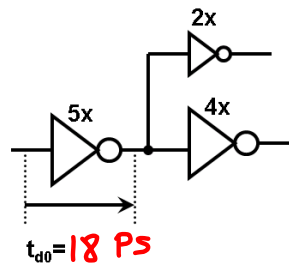
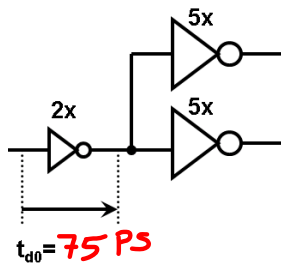
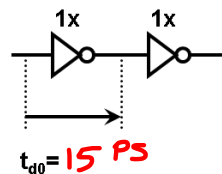
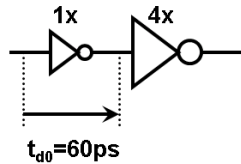
Exam 2

Name: Answers

Date: Nov. 12, 2012

Note: Only calculator, pencils, and pens are allowed.

1. (10 points) True or false:
- (a) It is always desirable to have a small noise margin. (**F**)
 - (b) To decrease t_{pHL} , the NMOS threshold voltage must be decreases. (**T**)
 - (c) When the input of a CMOS inverter is low, the leakage current will be determined by I_{OFF} of PMOS. (**F**)
 - (d) In a CMOS inverter, the slower input rise time results in lower short-circuit power. (**F**)
 - (e) A 10% reduction in power supply voltage reduces the dynamic power dissipation by about 20%. (**T**)
2. (15 points) Given the delay of a standard fanout-4 delay is 50ps (i.e. 1x inverter driving a 4x inverter), determine the delay in each of the following cases:



3. (10 points) Determine the $(W/L)_p$ of the PMOS transistor in a CMOS inverter such that the switching threshold voltage, V_M , becomes exactly $V_{DD}/2$. Assume that $K'_n=120\mu\text{A}/\text{V}^2$, $V_{tn}=0.3\text{V}$, $\lambda_n=0.01\text{V}^{-1}$, $(W/L)_n=10$, $K'_p=50\mu\text{A}/\text{V}^2$, $V_{tp}=-0.4\text{V}$, $\lambda_p=-0.02\text{V}^{-1}$ and $V_{DD}=1.2\text{V}$. Include the channel length modulation effect into your calculation.

$$\left(\frac{W}{L}\right)_p = 53.68$$

4. (10 points) Calculate the short circuit current, $I_{DD\text{Max}}$, in the CMOS inverter of problem 3. Again, include the channel length modulation effect into your calculation.

$$I_{DD\text{Max}} = 54.324 \mu\text{A}$$

5. (10 points) Using the slope of VTC curve (equation g below) determine V_{IL} and V_{IH} of the CMOS inverter in problem 3.

$$g = \frac{-2}{\lambda_n + |\lambda_p|} \left(\frac{1}{V_M - V_{Tn}} + \frac{1}{V_{DD} - V_M - |V_{Tp}|} \right)$$

$$g = -555.55$$

$$V_{IL} = 0.5989 \text{ V}$$

$$V_{IH} = 0.601 \text{ V}$$

6. (10 points) From the V_{IL} and V_{IH} found in Problem 5, determine the low and high noise margin of the CMOS inverter.

$$NM_L = NM_H = 0.5989 \text{ V}$$

7. (15 points) The output of the CMOS inverter in problem 3 is connected to a 100fF load capacitor. Use the average current technique to find high-to-low propagation delay, t_{pHL} . Include the channel length modulation effect only in saturation region, not in linear region.

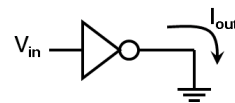
$$I_{av} = 461.916 \mu A$$

$$t_{pHL} = 129.89 \text{ pF}$$

8. (10 points) Determine the dynamic power consumption in the CMOS inverter of problem 7, if a square wave pulse running at 1GHz frequency is applied to its input.

$$P_D = 144 \mu W$$

9. (10 points) The output of the CMOS inverter in problem 3 has been connected to a defective load which is a short circuit to GND (see figure below). Determine the output current, I_{out} , when the input voltage, V_{in} , is zero and V_{DD} .



$$V_{in} = 0 \Rightarrow I_{out} = 879.5 \mu A$$

$$V_{in} = V_{DD} \Rightarrow I_{out} = 0$$